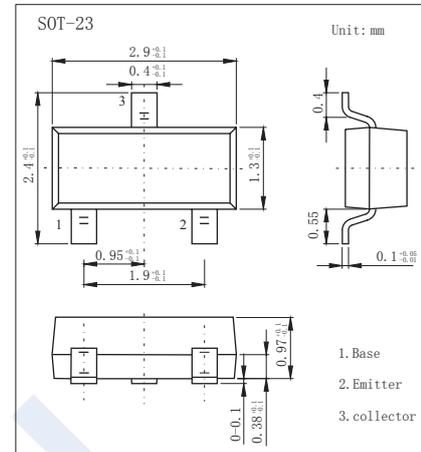


PNP Transistors

2SA2058

■ Features

- High DC current gain: $h_{FE} = 200$ to 500 ($I_C = -0.2$ A)
- Low collector-emitter saturation voltage:
 $V_{CE(sat)} = -0.19$ V (max)
- High-speed switching: $t_f = 25$ ns (typ.)



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|--|-----------|------------|------------------|
| Collector - Base Voltage | V_{CB0} | -20 | V |
| Collector - Emitter Voltage | V_{CE0} | -10 | |
| Emitter - Base Voltage | V_{EB0} | -7 | |
| Collector Current - Continuous | I_C | -1.5 | A |
| Collector Current - Pulse | I_{CP} | -2.5 | |
| Base Current | I_B | -150 | mA |
| Collector Power Dissipation $t=10\text{s}$ (Note.1) | P_C | 500 | mW |
| | | 750 | |
| Junction Temperature | T_J | 150 | $^\circ\text{C}$ |
| Storage Temperature range | T_{stg} | -55 to 150 | |

Note.1: Mounted on an FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm^2)

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|--|-----|-----|-------|---------------|
| Collector- base breakdown voltage | V_{CB0} | $I_C = -100\ \mu\text{A}$, $I_E = 0$ | -20 | | | V |
| Collector- emitter breakdown voltage | V_{CE0} | $I_C = -10\ \text{mA}$, $I_B = 0$ | -10 | | | |
| Emitter - base breakdown voltage | V_{EB0} | $I_E = -100\ \mu\text{A}$, $I_C = 0$ | -7 | | | |
| Collector-base cut-off current | I_{CBO} | $V_{CB} = -20\text{V}$, $I_E = 0$ | | | -0.1 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB} = -7\text{V}$, $I_C = 0$ | | | -0.1 | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -600\text{mA}$, $I_B = -20\text{mA}$ | | | -0.19 | V |
| Base - emitter saturation voltage | $V_{BE(sat)}$ | $I_C = -600\text{mA}$, $I_B = -20\text{mA}$ | | | -1.1 | |
| DC current gain | h_{FE} | $V_{CE} = -2\text{V}$, $I_C = -200\text{mA}$ | 200 | | 500 | |
| | | $V_{CE} = -2\text{V}$, $I_C = -600\text{mA}$ | 125 | | | |
| Rise Time | t_r | See Figure 1 circuit diagram. | | 50 | | ns |
| Storage Time | t_{stg} | $V_{CC} = -6\text{V}$, $R_L = 10\ \Omega$ | | 115 | | |
| Fall Time | t_f | $-I_{B1} = I_{B2} = -20\ \text{mA}$ | | 25 | | |
| Collector output capacitance | C_{ob} | $V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$ | | 12 | | pF |

■ Marking

| | |
|---------|----|
| Marking | WM |
|---------|----|

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■ Typical Characteristics

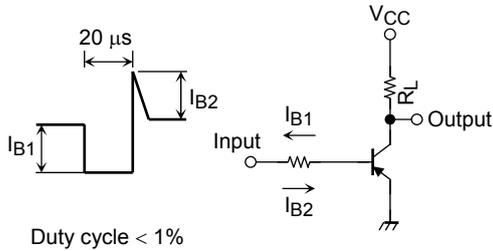
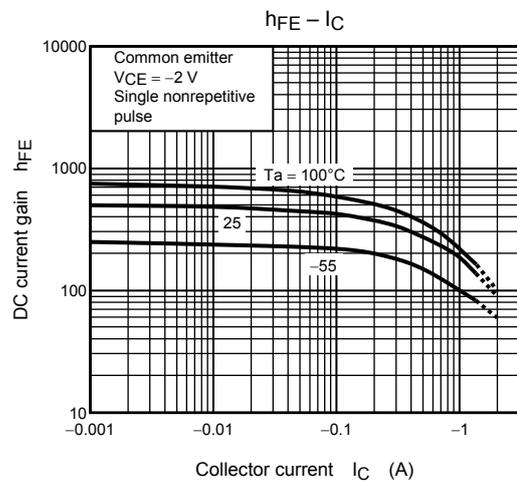
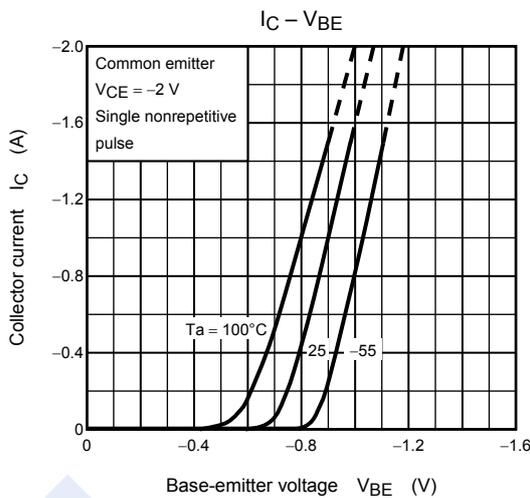
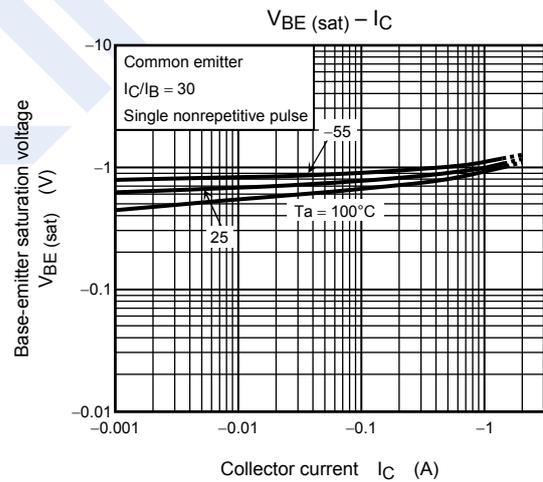
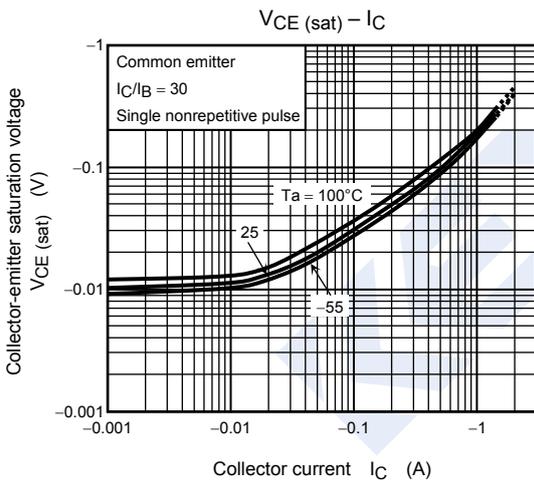
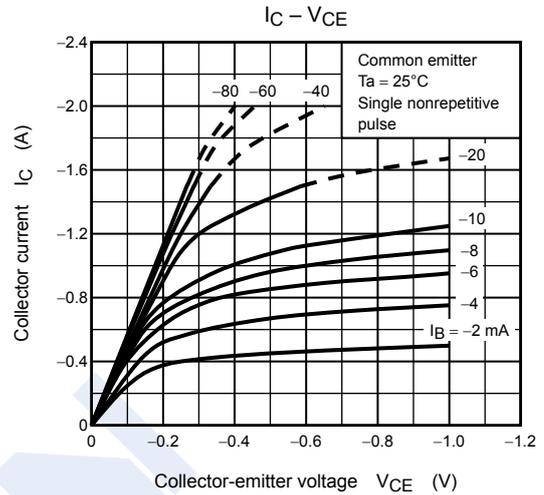


Figure 1 Switching Time Test Circuit & Timing Chart



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■ Typical Characteristics

